

- A
B
- (a) applying a coating layer of a chemically-amplified positive photoresist composition on a substrate, the photoresist composition comprising a phenolic resin and one or more photoacid generator compounds, the resin comprising at least three distinct repeat units;
- (b) exposing the photoresist coating layer to EUV radiation having a wavelength of less than about 160 nm, or electron beam or ion beam radiation.
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A²

7. (amended) The method of claim 1 or 2 wherein the one or more photoacid generator compounds are present in a concentration of at least about 6 weight percent based on weight of total solids of the photoresist composition.

8. (amended) The method of claim 1 or 2 wherein the one or more photoacid generator compounds are present in a concentration of at least about 8 weight percent based on weight of total solids of the photoresist composition.

9. (amended) The method of claim 1 or 2 wherein the one or more photoacid generator compounds are present in a concentration up to about 12 weight percent based on weight of total solids of the photoresist composition.

10. (amended) The method of claim 1 or 2 wherein the one or more photoacid generator compounds are present in a concentration of from about 10 to about 15 weight percent of total solids of the photoresist composition.

11. (amended) The method of claim 1 or 2 wherein the one or more photoacid generator compounds are ionic compounds.

12. (amended) The method of claim 1 or 2 wherein the one or more photoacid generator compounds are non-ionic compounds.